

# Interference Search

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	("field oxide" near "active area") and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4.clm.	US-PGPUB	OR	ON	2005/07/21 12:47
L2	2	("field oxide" near "active area") and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4.clm.	US-PGPUB	OR	ON	2005/07/21 12:52
L3	0	("field oxide" near "active area") and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4) and (438/48.ccls.)	US-PGPUB	OR	ON	2005/07/21 12:52
L4	348	438/48.ccls.	US-PGPUB	OR	ON	2005/07/21 12:52
L5	4	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type and implant\$4 and mask and photoresist and float\$4.clm.	US-PGPUB	OR	ON	2005/07/21 13:03